

MC74HCT244A

Octal 3-State Noninverting Buffer/Line Driver/ Line Receiver with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT244A is identical in pinout to the LS244. This device may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT244A is an octal noninverting buffer line driver line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has non-inverted outputs and two active-low output enables.

The HCT244A is the non-inverting version of the HCT240. See also HCT241.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1 μ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 112 FETs or 28 Equivalent Gates
- Pb-Free Packages are Available

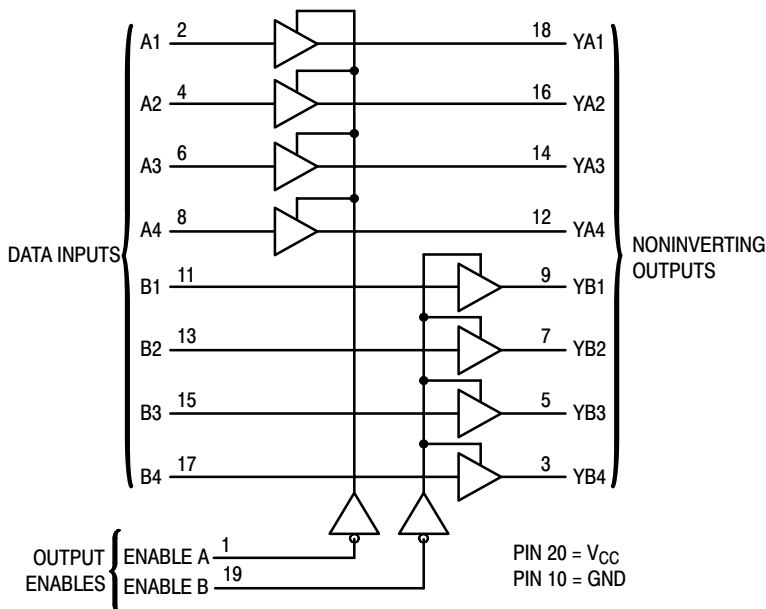
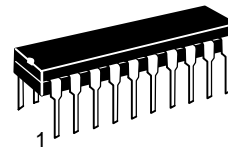


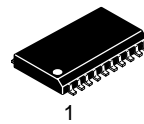
Figure 1. Logic Diagram



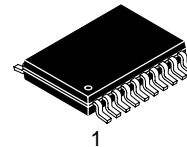
ON Semiconductor®



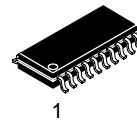
PDIP-20
N SUFFIX
CASE 738



SOIC-20W
DW SUFFIX
CASE 751D



TSSOP-20
DT SUFFIX
CASE 948E



SOEIAJ-20
M SUFFIX
CASE 967

PIN ASSIGNMENT

ENABLE A	1 ●	20	V _{CC}
A1	2	19	ENABLE B
YB4	3	18	YA1
A2	4	17	B4
YB3	5	16	YA2
A3	6	15	B3
YB2	7	14	YA3
A4	8	13	B2
YB1	9	12	YA4
GND	10	11	B1

FUNCTION TABLE

Inputs		Outputs
Enable A, Enable B	A, B	YA, YB
L	L	L
L	H	H
H	X	Z

Z = high impedance, X = don't care

ORDERING AND MARKING INFORMATION

See detailed ordering, shipping, and marking information in the package dimensions section on page 5 of this data sheet.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

†Derating – Plastic DIP: - 10 mW/°C from 65° to 125°C
 – SOIC Package: - 7 mW/°C from 65° to 125°C
 – TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5	2	2	2	V
			5.5	2	2	2	
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5	0.8	0.8	0.8	V
			5.5	0.8	0.8	0.8	
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	4.5	4.4	4.4	4.4	V
			5.5	5.4	5.4	5.4	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	4.5	0.1	0.1	0.1	V
			5.5	0.1	0.1	0.1	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	4.5	0.26	0.33	0.4	μA
			5.5	± 0.1	± 1.0	± 1.0	
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} ; V _{out} = V _{CC} or GND	5.5	± 0.5	± 5.0	± 10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5	4	40	160	μA
ΔI _{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs I _{out} = 0 μA	5.5	≥ -55°C	25°C to 125°C		mA
				2.9	2.4		

- Information on typical parametric values along with frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- Total Supply Current = I_{CC} + ΣΔI_{CC}.

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AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	Guaranteed Limit			Unit
		- 55 to 25 °C	≤ 85 °C	≤ 125 °C	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	20	25	30	ns
t_{PLZ} , t_{PHZ}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	26	33	39	ns
t_{PZL} , t_{PZH}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	22	28	33	ns
t_{TLH} , t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25 °C, $V_{CC} = 5.0 \text{ V}$		pF
		55		

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

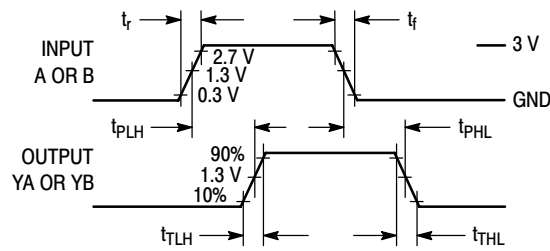


Figure 2.

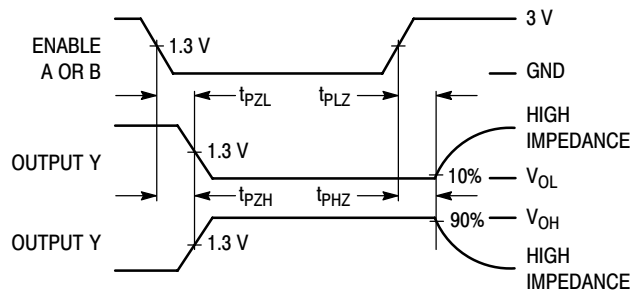


Figure 3.

MC74HCT244A

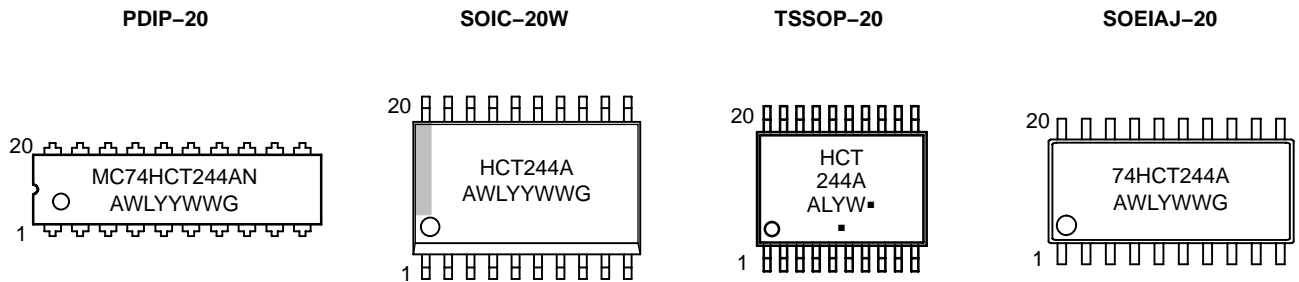
ORDERING INFORMATION

Device	Package	Shipping†
MC74HCT244AN	PDIP-20	18 Units / Rail
MC74HCT244ANG	PDIP-20 (Pb-Free)	
MC74HCT244ADW	SOIC-20	38 Units / Rail
MC74HCT244ADWG	SOIC-20 (Pb-Free)	
MC74HCT244ADWR2	SOIC-20	1000 / Tape & Reel
MC74HCT244ADWR2G	SOIC-20 (Pb-Free)	
MC74HCT244ADTR2	TSSOP-20*	2500 / Tape & Reel
MC74HCT244ADTR2G	TSSOP-20*	
MC74HCT244AF	SOEIAJ-20	40 Units / Rail
MC74HCT244AFG	SOEIAJ-20 (Pb-Free)	
MC74HCT244AFEL	SOEIAJ-20	2000 / Tape & Reel
MC74HCT244AFELG	SOEIAJ-20 (Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*These packages are inherently Pb-Free.

MARKING DIAGRAMS

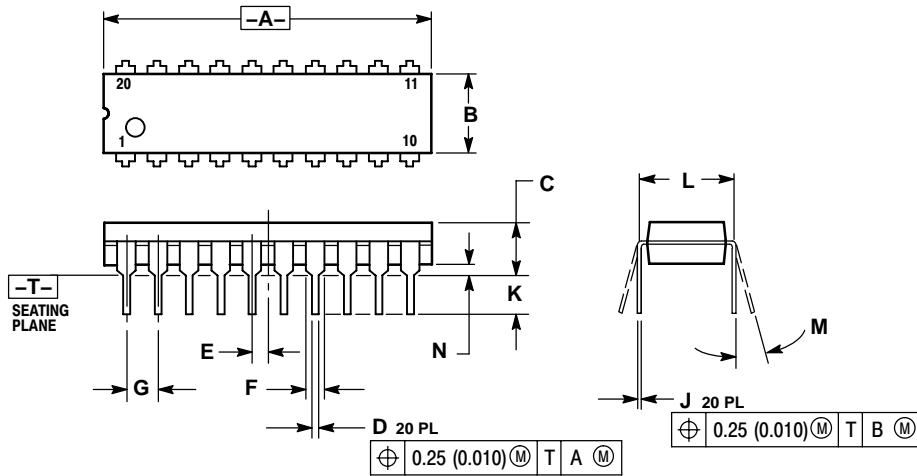


A = Assembly Location
 WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G or ■ = Pb-Free Package
 (Note: Microdot may be in either location)

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PACKAGE DIMENSIONS

PDIP-20
N SUFFIX
PLASTIC DIP PACKAGE
CASE 738-03
ISSUE E

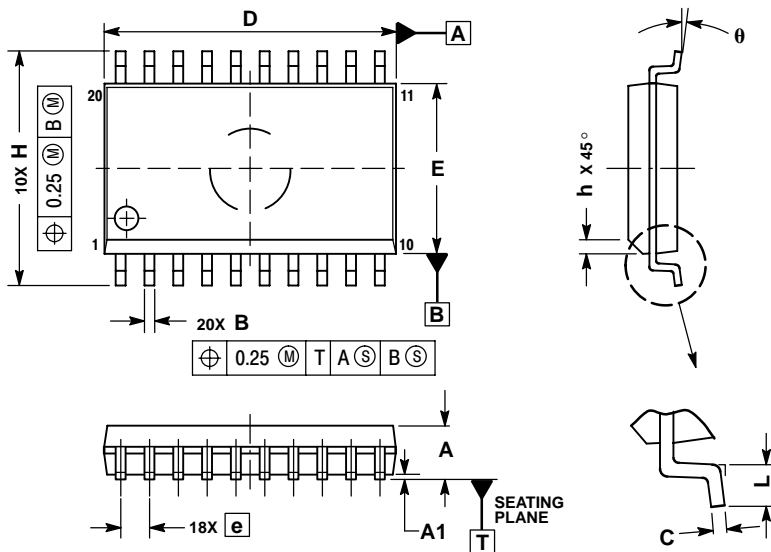


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

SOIC-20W
DW SUFFIX
CASE 751D-05
ISSUE G



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
theta	0°	7°